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# Author Index

Abad, J., C. Rogero, J. Méndez, M.F. López, J.A. Martín-Gago and E. Román, Growth of subnanometer-thin Si overlayer on $TiO_2$ (1 1 0)-(1 × 2) surface 234 (2004) 497
Ádám, M., see Horváth, Z.J. 234 (2004) 54
Aggarwal, I.D., see Cricenti, A. 234 (2004) 374
Akagi, K., S. Tsuneyuki, Y. Yamashita, K. Hamaguchi and J. Yoshinobu, Structural and chemical property of unsaturated cyclic-hydrocarbon molecules regularly chemisorbed on Si(0 0 1) surface 234 (2004) 162
Akimoto, K., see Yoshida, Y. 234 (2004) 409
Albuquerque, E.L., see Vasconcelos, M.S. 234 (2004) 33
Ares, J.R., see Pascual, A. 234 (2004) 355
Ascolani, H., see Dávila, M.E. 234 (2004) 274
Ascolani, H., see Izquierdo, M. 234 (2004) 468
Asensio, M.C., see Dávila, M.E. 234 (2004) 274
Asensio, M.C., see Izquierdo, M. 234 (2004) 468
Avila, J., see Dávila, M.E. 234 (2004) 274
Avila, J., see Izquierdo, M. 234 (2004) 468
Azuma, K., see Hattori, T. 234 (2004) 197

Baba, Y., see Nath, K.G. 234 (2004) 234
Baba, Y., T. Sekiguchi, I. Shimoyama and K.G. Nath, Electronic structures of ultra-thin silicon carbides deposited on graphite 234 (2004) 246
Bachir Bouiadjra, N., see Petit, M. 234 (2004) 451
Bae, C., and G. Lucovsky, Reductions in interface defects, $D_{it}$, by post-oxidation plasma-assisted nitridation of GaN–$SiO_2$ interfaces in MOS devices 234 (2004) 475
Bakarov, A.K., see Milekhin, A.G. 234 (2004) 45
Baldacchini, G., see Cricenti, A. 234 (2004) 374
Barber, Z.H., see Yan, J. 234 (2004) 328
Bechstedt, F., see Preuss, M. 234 (2004) 155
Bekkali, A., see Kampen, T. 234 (2004) 313
Bekkali, A.-E.-H., I. Thurzo, T.U. Kampen and D.R.T. Zahn, Impedance spectroscopy study of metal–organic–metal structures 234 (2004) 149
Benamara, Z., see Petit, M. 234 (2004) 451
Bernholc, J., see Fleischer, K. 234 (2004) 302
Bideux, L., see Petit, M. 234 (2004) 451
Biel, B., see Kampen, T. 234 (2004) 341
Bila, R.V., see Semchuk, O.Yu. 234 (2004) 415
Blood, P., see Brown, M.R. 234 (2004) 434
Bolognesi, A., see Kampen, T. 234 (2004) 313
Bonfigli, F., see Cricenti, A. 234 (2004) 374
Bongiorno, A., and A. Pasquarello, Atomistic model structure of the Si(1 0 0)–$SiO_2$ interface from a synthesis of experimental data 234 (2004) 190
Bozhko, S.I., A.N. Chaika, G.A. Emelchenko, V.M. Masalov, A.M. Ionov, A.N. Gruzintsev, G.M. Mikhailov and B.K. Medvedev, Mono- and multilayered opalline superlattices: application to nanotechnology of 2D ordered array of nanoobjects and 3D metalattices 234 (2004) 93
Brito-Orta, R.A., see Prutskij, T. 234 (2004) 462
Brown, M.R., K.S. Teng, A. Kestle, P. Smowton, P. Blood, P.A. Mawby and S.P. Wilks, Study of dual-valley transport across a multiquantum barrier to enhance carrier confinement 234 (2004) 434
Bushell, A., see Cabailh, G. 234 (2004) 144

Cabailh, G., J.W. Wells, I.T. McGovern, A.R. Vearey-Roberts, A. Bushell and D.A. Evans, Synchrotron radiation studies of the growth and beam damage of tin-phthalocyanine on GaAs(0 0 1)-1 × 6 substrates 234 (2004) 144
Cabailh, G., see Vearey-Roberts, A.R. 234 (2004) 131
Caetano, E.W.S., V.N. Freire, G.A. Farias and E.F. da Silva Jr., Optical properties of zinc-blende GaN/BN cylindrical nanowires 234 (2004) 50
Cerrillo, I., see Vearey-Roberts, A.R. 234 (2004) 131
Chaika, A.N., see Bozhko, S.I. 234 (2004) 93
Chandola, S., see Fleischer, K. 234 (2004) 302
Chiussi, S., see López, E. 234 (2004) 422
Cho, N.-H., see Kim, D.-A. 234 (2004) 256
Cho, N.-H., see Park, M.-B. 234 (2004) 78
Cho, N.-H., see Park, M.-B. 234 (2004) 487
Cho, N.-H., see Shim, J.-H. 234 (2004) 268
Chrost, J., see Izquierdo, M. 234 (2004) 468
Combellas, C., see Nešpúrek, S. 234 (2004) 395
Congiu-Castellano, A., see Cricenti, A. 234 (2004) 374
Cricenti, A., Longo, G., Ustione, A., Mussi, V., Generosi, R., Luce, M., Rinaldi, M., Perfetti, P., Vobornik, D., Margaritondo, G., Sanghera, J.S., Thielen, P., Aggarwal, I.D., Ivanov, B., Miller, J.K., Haglund, R., Tolk, N.H., Congiu-Castellano, A., Rizzo, M.A., Piston, D.W., Somma, F., Baldacchini, G., Bonfigli, F., Marolo, T., Flora, F., Montereali, R.M., Faenov, A. and T. Pikuz, Optical nanospectroscopy applications in material science 234 (2004) 374

doi:10.1016/S0169-4332(04)01140-7

da Silva Jr., E.F., see Caetano, E.W.S. 234 (2004) 50
da Silva Jr., E.F., see de Azevedo, W.M. 234 (2004) 457
da Silva Jr., E.F., see de Sousa, J.S. 234 (2004) 218
da Silva Jr., E.F., see Vasconcelos, M.S. 234 (2004) 33
Das, A., see Kampen, T.U. 234 (2004) 333
Dávila, M.E., J. Avila, H. Ascolani, G. Le Lay, M. Göthelid, U.O. Karlsson and M.C. Asensio, Surface phase transitions at interfaces: metal–semiconductor: a revisit is needed 234 (2004) 274
Dávila, M.E., see Izquierdo, M. 234 (2004) 468
Däweritz, L., see Moreno, M. 234 (2004) 16
Díaz-Arencibia, P., see Prutskij, T. 234 (2004) 462
de Azevedo, W.M., D.D. de Carvalho, E.A. de Vasconcelos and E.F. da Silva Jr., Photoluminescence characteristics of rare earth-doped nanoporous aluminum oxide 234 (2004) 457
de Carvalho, D.D., see de Azevedo, W.M. 234 (2004) 457
de Seqovia, J.L., see Flores, F. 234 (2004) 1
de Sousa, J.S., V.N. Freire and E.F. da Silva Jr., $\delta(r)$ type model for interface defects in Si/$SiO_2$ nanocrystals 234 (2004) 218
de Vasconcelos, E.A., see de Azevedo, W.M. 234 (2004) 457
Di Carlo, A., see Kampen, T. 234 (2004) 313
Dózsa, L., G. Molnár, Z.J. Horváth, A.L. Tóth, J. Gyulai, V. Raineri and F. Giannazzo, Investigation of the morphology and electrical characteristics of $FeSi_2$ quantum dots on silicon 234 (2004) 60
Dózsa, L., see Horváth, Z.J. 234 (2004) 67
Dulot, F., see Kraus, A. 234 (2004) 307
Dulot, F., see Wulfhekel, W. 234 (2004) 251

Ebest, G., see König, D. 234 (2004) 222
Emelchenko, G.A., see Bozhko, S.I. 234 (2004) 93
Emoto, T., see Yoshida, Y. 234 (2004) 409
Esser, N., see Fleischer, K. 234 (2004) 302
Evans, D.A., see Cabailh, G. 234 (2004) 144
Evans, D.A., see Vearey-Roberts, A.R. 234 (2004) 131
Evans, S., see Vearey-Roberts, A.R. 234 (2004) 131
Evtukh, A.A., see Litovchenko, V.G. 234 (2004) 262

Fabbri, F., see López, E. 234 (2004) 422
Faenov, A., see Cricenti, A. 234 (2004) 374
Farias, G.A., see Caetano, E.W.S. 234 (2004) 50
Farias, G.A., see Oliveira, C.L.N. 234 (2004) 38
Ferkel, H.S., Owen, G.T., T.G.G. Maffeïs, M. Penny, K.S. Teng and S.P. Wilks, Macroscopic and microscopic investigations of the effect of gas exposure on nanocrystalline $SnO_2$ at elevated temperature 234 (2004) 82
Ferkel, H.S., T.G.G. Maffeis, G.T. Owen, M. Penny and S.P. Wilks, STM patterning of $SnO_2$ nanocrystalline surfaces 234 (2004) 2
Ferraz, A.C., and R. Miotto, Adsorption and decomposition of acetone on Si(0 0 1) 234 (2004) 185
Ferrer, D., T. Shinada, T. Tanii, J. Kurosawa, G. Zhong, Y. Kubo, S. Okamoto, H. Kawarada and I. Ohdomari, Selective growth of carbon nanostructures on nickel implanted nanopyramid array 234 (2004) 72
Ferrer, I.J., see Pascual, A. 234 (2004) 355
Fitzgerald, A.G., see Romero, J.S. 234 (2004) 369
Fleischer, K., S. Chandola, N. Esser, W. Richter, J.F. McGilp, W.G. Schmidt, S. Wang, W. Lu and J. Bernholc, Atomic indium nanowires on Si(1 1 1): the (4 × 1)–(8 × 2) phase transition studied with reflectance anisotropy spectroscopy 234 (2004) 302
Flora, F., see Cricenti, A. 234 (2004) 374
Flores, F., and J.L. de Seqovia, Foreword 234 (2004) 1
Flores, F., see Kaminski, W. 234 (2004) 286
Flores, F., see Kampen, T. 234 (2004) 341
Flores, F., see Vázquez, H. 234 (2004) 107
Fornarini, L., see López, E. 234 (2004) 422
Frauenheim, Th., see Szűcs, B. 234 (2004) 173
Freire, J.A.K., see Oliveira, C.L.N. 234 (2004) 38
Freire, V.N., see Caetano, E.W.S. 234 (2004) 50
Freire, V.N., see de Sousa, J.S. 234 (2004) 218
Freire, V.N., see Oliveira, C.L.N. 234 (2004) 38
Freire, V.N., see Vasconcelos, M.S. 234 (2004) 33
Friedrich, M., see Silaghi, S.D. 234 (2004) 113
Fritsche, R., B. Jaeckel, A. Klein and W. Jaegermann, High-resolution photoemission study of the Si(111)/Au interface and its modification by a GaSe van der Waals termination layer 234 (2004) 321
Fulton, C., see Hinkle, C.L. 234 (2004) 240
Funatsu, T., see Tanii, T. 234 (2004) 102

Galzerani, J.C., see Milekhin, A.G. 234 (2004) 45
Gavrila, G., H. Méndez, T.U. Kampen and D.R.T. Zahn, Changes in the electronic structure of DiMePTCDI films on S-GaAs(1 0 0) upon exposure to oxygen 234 (2004) 126
Generosi, R., see Cricenti, A. 234 (2004) 374
Giannazzo, F., see Dózsa, L. 234 (2004) 60
Ginev, G., T. Riedl, R. Parashkov, H.-H. Johannes and W. Kowalsky, Organic-GaAs heterostructure diodes for microwave applications 234 (2004) 22
González, P., see López, E. 234 (2004) 422
Gorbanyuk, T.I., see Litovchenko, V.G. 234 (2004) 262
Gorgoi, M., W. Michaelis, T.U. Kampen, D. Schlettwein and D.R.T. Zahn, Thickness dependence of the LUMO position for phthalocyanines on hydrogen passivated silicon (1 1 1) 234 (2004) 138
Göthelid, M., see Dávila, M.E. 234 (2004) 274
Gruzintsev, A.N., see Bozhko, S.I. 234 (2004) 93
Gruzza, B., see Petit, M. 234 (2004) 451
Gyulai, J., see Dózsa, L. 234 (2004) 60

Haglund, R., see Cricenti, A. 234 (2004) 374
Hajnal, Z., see Szűcs, B. 234 (2004) 173
Hamaguchi, K., see Akagi, K. 234 (2004) 162
Han, K.-H., see Park, M.-B. 234 (2004) 78
Hanbücken, M., see Kraus, A. 234 (2004) 307
Hanbücken, M., see Wulfhekel, W. 234 (2004) 251
Hasegawa, H., see Hashizume, T. 234 (2004) 387
Hasegawa, H., see Sato, T. 234 (2004) 11

Hashizume, T., and H. Hasegawa, Effects of nitrogen deficiency on electronic properties of AlGaN surfaces subjected to thermal and plasma processes 234 (2004) 387
Hattori, T., K. Azuma, Y. Nakata, M. Shioji, T. Shiraishi, T. Yoshida, K. Takahashi, H. Nohira, Y. Takata, S. Shin and K. Kobayashi, Dependence of $SiO_2$/Si interface structure on low-temperature oxidation process 234 (2004) 197
Hattori, T., see Hirose, K. 234 (2004) 202
Hattori, T., see Nohira, H. 234 (2004) 493
Heyes, C.D., see Kobitski, A.Yu. 234 (2004) 86
Hinkle, C.L., C. Fulton, R.J. Nemanich and G. Lucovsky, Enhanced tunneling in stacked gate dielectrics with ultra-thin $HfO_2$ layers sandwiched between thicker $SiO_2$ layers 234 (2004) 240
Hinkle, C.L., see Lucovsky, G. 234 (2004) 429
Hirose, K., S. Kawashiri and T. Hattori, XPS analysis of carrier trapping phenomena in ultrathin $SiO_2$ film formed on Si substrate 234 (2004) 202
Hong, J.G., see Lucovsky, G. 234 (2004) 429
Horváth, Z.J., L. Dózsa, O.H. Krafcsik, T. Mohácsy and G.y. Vida, Electrical behaviour of Al/$SiO_2$/Si structures with SiC nanocrystals 234 (2004) 67
Horváth, Z.J., M. Ádám, I. Szabó, L.K. Orlov, A.V. Potapov and V.A. Tolomasov, Electrical behaviour of Al/SiGe/Si heterostructures: effect of surface treatment and dislocations 234 (2004) 54
Horváth, Z.J., see Dózsa, L. 234 (2004) 60
Horváth, Z.J., see Osvald, J. 234 (2004) 349
Hosaka, T., see Tanii, T. 234 (2004) 102
Hoyer, W., see Kampen, T.U. 234 (2004) 333
Huang, S., Y. Tian and F. Lu, Investigation on the barrier height and phase transformation of nickel silicide Schottky contact 234 (2004) 362
Humphreys, C.J., see Yan, J. 234 (2004) 328

Ichimiya, A., see Nakahara, H. 234 (2004) 292
Im, S., see Shim, J.-H. 234 (2004) 268
Ionov, A.M., see Bozhko, S.I. 234 (2004) 93
Itagaki, K., see Yoshida, Y. 234 (2004) 409
Ivanov, B., see Cricenti, A. 234 (2004) 374
Ivanov, S.V., see Sitnikova, A.A. 234 (2004) 28
Iwai, H., see Nohira, H. 234 (2004) 493
Izquierdo, M., M.E. Dávila, C.M. Teodorescu, J. Chrost, H. Ascolani, J. Avila and M.C. Asensio, Influence of the substrate surface termination on the properties of bcc-cobalt films: GaAs(1 1 0) versus Sb/GaAs(1 1 0) 234 (2004) 468

Jaeckel, B., see Fritsche, R. 234 (2004) 321
Jaegermann, W., see Fritsche, R. 234 (2004) 321
Jelinek, P., see Kaminski, W. 234 (2004) 286
Jiménez-Rodríguez, J.J., see Mari Carmen Pérez-Martín, A. 234 (2004) 228
Jiménez-Sáez, J.C., see Mari Carmen Pérez-Martín, A. 234 (2004) 228
Johannes, H.-H., see Ginev, G. 234 (2004) 22
Joumori, S., see Nohira, H. 234 (2004) 493

Kahn, A., see Vázquez, H. 234 (2004) 107
Kaminski, W., P. Jelinek, R. Pérez, F. Flores and J. Ortega, Si-substitutional defects on the $\alpha$-Sn/Si(1 1 1)-($\sqrt{3} \times \sqrt{3}$) surface 234 (2004) 286
Kampen, T., A. Bekkali, I. Thurzo, D.R.T. Zahn, A. Bolognesi, T. Ziller, A. Di Carlo and P. Lugli, Barrier heights of organic modified Schottky contacts: theory and experiment 234 (2004) 313
Kampen, T., A. Schüller, D.R.T. Zahn, B. Biel, J. Ortega, R. Pérez and F. Flores, Schottky contacts on passivated GaAs(1 0 0) surfaces: barrier height and reactivity 234 (2004) 341
Kampen, T.U., A. Das, S. Park, W. Hoyer and D.R.T. Zahn, Relation between morphology and work function of metals deposited on organic substrates 234 (2004) 333
Kampen, T.U., see Bekkali, A.-E.-H. 234 (2004) 149
Kampen, T.U., see Gavrila, G. 234 (2004) 126
Kampen, T.U., see Gorgoi, M. 234 (2004) 138
Kampen, T.U., see Paez, B.A. 234 (2004) 168
Kampen, T.U., see Salvan, G. 234 (2004) 178
Kampen, T.U., see Silaghi, S.D. 234 (2004) 113
Kang, D., see Lucovsky, G. 234 (2004) 429
Kappers, M.J., see Yan, J. 234 (2004) 328
Karlsson, U.O., see Dávila, M.E. 234 (2004) 274
Karlsteen, M., see Semchuk, O.Yu. 234 (2004) 415
Kashiwagi, I., see Nohira, H. 234 (2004) 493
Kawarada, H., see Ferrer, D. 234 (2004) 72
Kawashiri, S., see Hirose, K. 234 (2004) 202
Kestle, A., see Brown, M.R. 234 (2004) 434
Kikuchi, S., see Yoshida, Y. 234 (2004) 409
Kim, D.-A., J.-H. Shim and N.-H. Cho, PL and EL features of p-type porous silicon prepared by electrochemical anodic etching 234 (2004) 256
Kimura, K., see Nohira, H. 234 (2004) 493
Klein, A., see Fritsche, R. 234 (2004) 321
Kobayashi, K., see Hattori, T. 234 (2004) 197
Kobitski, A.Yu., C.D. Heyes and G.U. Nienhaus, Total internal reflection fluorescence microscopy—a powerful tool to study single quantum dots 234 (2004) 86
König, D., D.R.T. Zahn and G. Ebest, Field effect of fixed negative charges on oxidized silicon induced by $AlF_3$ layers with fluorine deficiency 234 (2004) 222
Konnikov, S.G., see Sitnikova, A.A. 234 (2004) 28
Kosch, U., see López, E. 234 (2004) 422
Kosel, T., see Prutskij, T. 234 (2004) 462
Kowalsky, W., see Ginev, G. 234 (2004) 22
Krafcsik, O.H., see Horváth, Z.J. 234 (2004) 67
Kraus, A., H. Neddermeyer, W. Wulfhekel, D. Sander, T. Maroutian, F. Dulot, A. Martinez-Gil and M. Hanbücken, Comparison of structural re-organisations observed on prepatterned vicinal Si(1 1 1) and Si(1 0 0) surfaces during heat treatment 234 (2004) 307

Kubo, Y., see Ferrer, D. 234 (2004) 72
Kurosawa, J., see Ferrer, D. 234 (2004) 72

Ladanov, M.Yu., see Milekhin, A.G. 234 (2004) 45
Le Lay, G., see Dávila, M.E. 234 (2004) 274
León, B., see López, E. 234 (2004) 422
Leycuras, A., see Wulfhekel, W. 234 (2004) 251
Lifshits, V.G., see Tsukanov, D.A. 234 (2004) 297
Litovchenko, V.G., T.I. Gorbanyuk, V.S. Solntsev and A.A. Evtukh, Mechanism of hydrogen, oxygen and humidity sensing by Cu/Pd-porous silicon–silicon structures 234 (2004) 262
Longo, G., see Cricenti, A. 234 (2004) 374
López, E., S. Chiussi, J. Serra, P. González, C. Serra, U. Kosch, B. León, F. Fabbri, L. Fornarini and S. Martelli, Growth and modification of thin SiGeC films at low substrate temperatures through UV laser assisted processing 234 (2004) 422
López, M.F., see Abad, J. 234 (2004) 497
Lu, F., see Huang, S. 234 (2004) 362
Lu, W., see Fleischer, K. 234 (2004) 302
Lublinskaya, O.G., see Sitnikova, A.A. 234 (2004) 28
Luce, M., see Cricenti, A. 234 (2004) 374
Lucovsky, G., G.B. Rayner, D. Kang, C.L. Hinkle and J.G. Hong, A spectroscopic study distinguishing between chemical phase separation with different degrees of crystallinity in Hf(Zr) silicate alloys 234 (2004) 429
Lucovsky, G., see Bae, C. 234 (2004) 475
Lucovsky, G., see Hinkle, C.L. 234 (2004) 240
Lugli, P., see Kampen, T. 234 (2004) 313

Maffeis, T.G.G., see Ferkel, H.S. 234 (2004) 2
Maffeïs, T.G.G., see Ferkel, H.S. 234 (2004) 82
Margaritondo, G., see Cricenti, A. 234 (2004) 374
Mari Carmen Pérez-Martín, A., J.J. Jiménez-Rodríguez and J.C. Jiménez-Sáez, Shallow boron dopant on silicon. An MD study 234 (2004) 228
Marolo, T., see Cricenti, A. 234 (2004) 374
Maroutian, T., see Kraus, A. 234 (2004) 307
Martelli, S., see López, E. 234 (2004) 422
Martinez-Gil, A., see Kraus, A. 234 (2004) 307
Martín-Gago, J.A., see Abad, J. 234 (2004) 497
Masalov, V.M., see Bozhko, S.I. 234 (2004) 93
Massies, J., see Vézian, S. 234 (2004) 445
Matolin, V., see Petit, M. 234 (2004) 451
Mauriz, P.W., see Vasconcelos, M.S. 234 (2004) 33
Mawby, P.A., see Brown, M.R. 234 (2004) 434
McGilp, J.F., see Fleischer, K. 234 (2004) 302
McGovern, I.T., see Cabailh, G. 234 (2004) 144
McGovern, I.T., see Vearey-Roberts, A.R. 234 (2004) 131
Medvedev, B.K., see Bozhko, S.I. 234 (2004) 93
Méndez, H., see Gavrila, G. 234 (2004) 126
Méndez, J., see Abad, J. 234 (2004) 497
Mendez, J., see Vearey-Roberts, A.R. 234 (2004) 131
Merz, J., see Prutskij, T. 234 (2004) 462
Michaelis, W., see Gorgoi, M. 234 (2004) 138
Mikhailov, G.M., see Bozhko, S.I. 234 (2004) 93
Milekhin, A.G., A.I. Toropov, A.K. Bakarov, M.Yu. Ladanov, G. Zanelatto, J.C. Galzerani, S. Schulze and D.R.T. Zahn, Optical phonons in InAs and AlAs quantum dot structures 234 (2004) 45
Miller, J.K., see Cricenti, A. 234 (2004) 374
Mintairov, A., see Prutskij, T. 234 (2004) 462
Miotto, R., see Ferraz, A.C. 234 (2004) 185
Miyake, T., see Tanii, T. 234 (2004) 102
Mohácsy, T., see Horváth, Z.J. 234 (2004) 67
Molnár, G., see Dózsa, L. 234 (2004) 60
Montereali, R.M., see Cricenti, A. 234 (2004) 374
Moreno, M., A. Trampert, L. Däweritz and K.H. Ploog, MnAs nanoclusters embedded in GaAs: synthesis and properties 234 (2004) 16
Mussi, V., see Cricenti, A. 234 (2004) 374

Nakahara, H., T. Suzuki and A. Ichimiya, Ag/Si(1 1 1)$\sqrt{3} \times \sqrt{3}$ surface phase transition at low temperature studied by RHEED 234 (2004) 292
Nakajima, K., see Nohira, H. 234 (2004) 493
Nakata, Y., see Hattori, T. 234 (2004) 197
Namgung, C., see Park, M.-B. 234 (2004) 78
Namita, H., see Yoshida, Y. 234 (2004) 409
Nannarone, S., see Sokolov, N.S. 234 (2004) 480
Natali, F., see Vézian, S. 234 (2004) 445
Nath, K.G., I. Shimoyama, T. Sekiguchi and Y. Baba, Study of the oxidation for Si nanostructures using synchrotron radiation photoemission spectroscopy 234 (2004) 234
Nath, K.G., see Baba, Y. 234 (2004) 246
Neddermeyer, H., see Kraus, A. 234 (2004) 307
Nemanich, R.J., see Hinkle, C.L. 234 (2004) 240
Nešpůrek, S., J. Sworakowski, C. Combellas, G. Wang and M. Weiter, A molecular device based on light controlled charge carrier mobility 234 (2004) 395
Nienhaus, G.U., see Kobitski, A.Yu. 234 (2004) 86
Nitsche, S., see Wulfhekel, W. 234 (2004) 251
Nohira, H., see Hattori, T. 234 (2004) 197
Nohira, H., T. Shiraishi, K. Takahashi, T. Hattori, I. Kashiwagi, C. Ohshima, S. Ohmi, H. Iwai, S. Joumori, K. Nakajima, M. Suzuki and K. Kimura, Atomic-scale depth profiling of composition, chemical structure and electronic band structure of $La_2O_3$/Si(1 0 0) interfacial transition layer 234 (2004) 493

O'Brien, S., see Vearey-Roberts, A.R. 234 (2004) 131
Ohdomari, I., see Ferrer, D. 234 (2004) 72
Ohdomari, I., see Tanii, T. 234 (2004) 102
Ohdomari, I., see Watanabe, T. 234 (2004) 207
Ohmi, S., see Nohira, H. 234 (2004) 493
Ohshima, C., see Nohira, H. 234 (2004) 493
Okamoto, S., see Ferrer, D. 234 (2004) 72
Okamura, Y., see Sakaue, H. 234 (2004) 439
Oliveira, C.L.N., J.A.K. Freire, V.N. Freire and G.A. Farias, Inhomogeneous broadening arising from interface fluctuations in strained $In_xGa_{1-x}As$/GaAs and $(In_yGa_{1-y}As)_x(InP)_{1-x}$/InP quantum wells 234 (2004) 38

Orlov, L.K., see Horváth, Z.J. 234 (2004) 54
Ortega, J., see Kaminski, W. 234 (2004) 286
Ortega, J., see Kampen, T. 234 (2004) 341
Ortega, J., see Vázquez, H. 234 (2004) 107
Osvald, J., and Z.J. Horváth, Theoretical study of the temperature dependence of electrical characteristics of Schottky diodes with an inverse near-surface layer 234 (2004) 349
Oszwaldowski, R., see Vázquez, H. 234 (2004) 107
Owen, G.T., see Ferkel, H.S. 234 (2004) 2
Owen, G.T., see Ferkel, H.S. 234 (2004) 82

Paez, B., see Salvan, G. 234 (2004) 178
Paez, B.A., G. Salvan, S. Silaghi, R. Scholz, T.U. Kampen and D.R.T. Zahn, Raman monitoring of In and Ag growth on PTCDA and DiMe-PTCDI thin films 234 (2004) 168
Parashkov, R., see Ginev, G. 234 (2004) 22
Park, M.-B., and N.-H. Cho, Effect of sintering time on the chemical and electrical features of the grain boundary of the semiconducting $SrTiO_3$ ceramics synthesized from surface-coated powders 234 (2004) 487
Park, M.-B., K.-H. Han, J.-H. Shim, C. Namgung and N.-H. Cho, Effect of rare earth ions-doping on the chemical and optical features of nano-crystalline (Er, Tb:) Si thin films 234 (2004) 78
Park, S., see Kampen, T.U. 234 (2004) 333
Pascual, A., J.R. Ares, I.J. Ferrer and C.R. Sánchez, Electrical resistance evolution of Fe thin films during their sulphuration process 234 (2004) 355
Pasquali, L., see Sokolov, N.S. 234 (2004) 480
Pasquarello, A., see Bongiorno, A. 234 (2004) 190
Penny, M., see Ferkel, H.S. 234 (2004) 2
Penny, M., see Ferkel, H.S. 234 (2004) 82
Pérez, R., see Kaminski, W. 234 (2004) 286
Pérez, R., see Kampen, T. 234 (2004) 341
Pérez, R., see Vázquez, H. 234 (2004) 107
Perfetti, P., see Cricenti, A. 234 (2004) 374
Petit, M., Ch. Robert-Goumet, L. Bideux, B. Gruzza, Z. Benamara, N. Bachir Bouiadjra and V. Matolin, Auger electronic spectroscopy and electrical characterisation of InP(100) surfaces passivated by $N_2$ plasma 234 (2004) 451
Pikuz, T., see Cricenti, A. 234 (2004) 374
Piston, D.W., see Cricenti, A. 234 (2004) 374
Ploog, K.H., see Moreno, M. 234 (2004) 16
Plotnikov, V., see Zamoryarskaya, M.V. 234 (2004) 214
Potapov, A.V., see Horváth, Z.J. 234 (2004) 54
Preuss, M., W.G. Schmidt, K. Seino and F. Bechstedt, Methylchloride adsorbed on Si(0 0 1): an ab initio study 234 (2004) 155
Prutskij, T., P. Díaz-Arencibia, R.A. Brito-Orta, A. Mintairov, T. Kosel and J. Merz, Polarization anisotropy in the photoluminescence from InGaP layers grown by liquid phase epitaxy 234 (2004) 462

Raineri, V., see Dózsa, L. 234 (2004) 60
Rayner, G.B., see Lucovsky, G. 234 (2004) 429
Richter, W., see Fleischer, K. 234 (2004) 302
Riedl, T., see Ginev, G. 234 (2004) 22
Rinaldi, M., see Cricenti, A. 234 (2004) 374
Rizzo, M.A., see Cricenti, A. 234 (2004) 374
Robert-Goumet, Ch., see Petit, M. 234 (2004) 451
Rogero, C., see Abad, J. 234 (2004) 497
Román, E., see Abad, J. 234 (2004) 497
Romero, J.S., A.G. Fitzgerald and M.J. Rose, A transmission electron microscope study of metal/chalcogenide amorphous thin films 234 (2004) 369
Rose, M.J., see Romero, J.S. 234 (2004) 369
Ryjkov, S.V., see Tsukanov, D.A. 234 (2004) 297
Rykhova, O.V., see Sitnikova, A.A. 234 (2004) 28

Sakata, O., see Tajiri, H. 234 (2004) 403
Sakaue, H., Y. Taniguchi, Y. Okamura, S. Shingubara and T. Takahagi, Wet treatment for preparing atomically smooth Si(1 0 0) wafer surface 234 (2004) 439
Salvan, G., S. Silaghi, B. Paez, T.U. Kampen and D.R.T. Zahn, Modification of GaAs(1 0 0) surfaces upon adsorption of perylene derivatives 234 (2004) 178
Salvan, G., see Paez, B.A. 234 (2004) 168
Salvan, G., see Silaghi, S.D. 234 (2004) 113
Sánchez, C.R., see Pascual, A. 234 (2004) 355
Sander, D., see Kraus, A. 234 (2004) 307
Sander, D., see Wulfhekel, W. 234 (2004) 251
Sanghera, J.S., see Cricenti, A. 234 (2004) 374
Sanna, S., see Szűcs, B. 234 (2004) 173
Sato, T., I. Tamai, S. Yoshida and H. Hasegawa, Evolution mechanism of heterointerface cross-section during growth of GaAs ridge quantum wires by selective molecular beam epitaxy 234 (2004) 11
Schlettwein, D., see Gorgoi, M. 234 (2004) 138
Schmidt, W.G., see Fleischer, K. 234 (2004) 302
Schmidt, W.G., see Preuss, M. 234 (2004) 155
Scholz, R., see Paez, B.A. 234 (2004) 168
Scholz, R., see Silaghi, S.D. 234 (2004) 113
Scholz, R., see Szűcs, B. 234 (2004) 173
Schüller, A., see Kampen, T. 234 (2004) 341
Schulze, S., see Milekhin, A.G. 234 (2004) 45
Seino, K., see Preuss, M. 234 (2004) 155
Sekiguchi, T., see Baba, Y. 234 (2004) 246
Sekiguchi, T., see Nath, K.G. 234 (2004) 234
Selvaggi, G., see Sokolov, N.S. 234 (2004) 480
Semchuk, O.Yu., R.V. Bila, M. Willander and M. Karlsteen, Features of coherent laser beams interaction with condensed matter 234 (2004) 415
Semond, F., see Vézian, S. 234 (2004) 445
Serra, C., see López, E. 234 (2004) 422
Serra, J., see López, E. 234 (2004) 422
Shim, J.-H., S. Im and N.-H. Cho, Nanostructural features of nc-Si:H thin films prepared by PECVD 234 (2004) 268
Shim, J.-H., see Kim, D.-A. 234 (2004) 256

Shim, J.-H., see Park, M.-B. 234 (2004) 78
Shimoyama, I., see Baba, Y. 234 (2004) 246
Shimoyama, I., see Nath, K.G. 234 (2004) 234
Shin, S., see Hattori, T. 234 (2004) 197
Shinada, T., see Ferrer, D. 234 (2004) 72
Shingubara, S., see Sakaue, H. 234 (2004) 439
Shioji, M., see Hattori, T. 234 (2004) 197
Shiraishi, T., see Hattori, T. 234 (2004) 197
Shiraishi, T., see Nohira, H. 234 (2004) 493
Silaghi, S., see Paez, B.A. 234 (2004) 168
Silaghi, S., see Salvan, G. 234 (2004) 178
Silaghi, S.D., R. Scholz, G. Salvan, Y.J. Suzuki, M. Friedrich, T.U. Kampen and D.R.T. Zahn, Metal deposition onto biomolecular layers on silicon surfaces: a study of interface formation using Raman spectroscopy 234 (2004) 113
Sitnikova, A.A., O.G. Lublinskaya, A.A Toropov, O.V. Rykhova, S.G. Konnikov and S.V. Ivanov, TEM study of GaAs/GaSb QD heterostructures 234 (2004) 28
Smowton, P., see Brown, M.R. 234 (2004) 434
Sokolov, N.S., S.M. Suturin, V.P. Ulin, L. Pasquali, G. Selvaggi and S. Nannarone, Initial stages of MBE growth and formation of $CaF_2$/Si(0 0 1) high-temperature interface 234 (2004) 480
Sokolov, V.I., see Zamoryarskaya, M.V. 234 (2004) 214
Solntsev, V.S., see Litovchenko, V.G. 234 (2004) 262
Somma, F., see Cricenti, A. 234 (2004) 374
Steiner, H.J., see Vearey-Roberts, A.R. 234 (2004) 131
Suturin, S.M., see Sokolov, N.S. 234 (2004) 480
Suzuki, M., see Nohira, H. 234 (2004) 493
Suzuki, T., see Nakahara, H. 234 (2004) 292
Suzuki, Y.J., see Silaghi, S.D. 234 (2004) 113
Sworakowski, J., see Nešpůrek, S. 234 (2004) 395
Szabó, I., see Horváth, Z.J. 234 (2004) 54
Szűcs, B., Z. Hajnal, R. Scholz, S. Sanna and Th. Frauenheim, Theoretical study of the adsorption of a PTCDA monolayer on S-passivated GaAs(1 0 0) 234 (2004) 173

Tajiri, H., O. Sakata and T. Takahashi, Surface X-ray diffraction in transmission geometry 234 (2004) 403
Takahagi, T., see Sakaue, H. 234 (2004) 439
Takahashi, K., see Hattori, T. 234 (2004) 197
Takahashi, K., see Nohira, H. 234 (2004) 493
Takahashi, T., see Tajiri, H. 234 (2004) 403
Takata, Y., see Hattori, T. 234 (2004) 197
Tamai, I., see Sato, T. 234 (2004) 11
Taniguchi, Y., see Sakaue, H. 234 (2004) 439
Tanii, T., see Ferrer, D. 234 (2004) 72
Tanii, T., T. Hosaka, T. Miyake, G.-J. Zhang, T. Zako, T. Funatsu and I. Ohdomari, Preferential immobilization of biomolecules on silicon microstructure array by means of electron beam lithography on organosilane self-assembled monolayer resist 234 (2004) 102
Tatsumura, K., see Watanabe, T. 234 (2004) 207
Teng, K.S., see Brown, M.R. 234 (2004) 434
Teng, K.S., see Ferkel, H.S. 234 (2004) 82
Teodorescu, C.M., see Izquierdo, M. 234 (2004) 468
Thielen, P., see Cricenti, A. 234 (2004) 374
Thurzo, I., see Bekkali, A.-E.-H. 234 (2004) 149
Thurzo, I., see Kampen, T. 234 (2004) 313
Tian, Y., see Huang, S. 234 (2004) 362
Tolk, N.H., see Cricenti, A. 234 (2004) 374
Tolomasov, V.A., see Horváth, Z.J. 234 (2004) 54
Toropov, A.A, see Sitnikova, A.A. 234 (2004) 28
Toropov, A.I., see Milekhin, A.G. 234 (2004) 45
Tóth, A.L., see Dózsa, L. 234 (2004) 60
Trampert, A., see Moreno, M. 234 (2004) 16
Tsukanov, D.A., S.V. Ryjkov, O.A. Utas and V.G. Lifshits, The formation of Si(1 1 1)5 × 2–Au single-domain surface phase by a surface diffusion 234 (2004) 297
Tsuneyuki, S., see Akagi, K. 234 (2004) 162

Ulin, V.P., see Sokolov, N.S. 234 (2004) 480
Ustione, A., see Cricenti, A. 234 (2004) 374
Utas, O.A., see Tsukanov, D.A. 234 (2004) 297

van Elsbergen, V., C. Weijtens and J. Zaumseil, Interaction of caesium with poly(*p*-phenylene vinylene) suffaces 234 (2004) 120
Vasconcelos, M.S., P.W. Mauriz, E.L. Albuquerque, E.F. da Silva Jr. and V.N. Freire, Electronic spectra of GaAs/$Ga_xAl_{1-x}As$ superlattice with impurities arranged according to a Fibonacci sequence 234 (2004) 33
Vázquez, H., F. Flores, R. Oszwaldowski, J. Ortega, R. Pérez and A. Kahn, Barrier formation at metal–organic interfaces: dipole formation and the charge neutrality level 234 (2004) 107
Vearey-Roberts, A.R., H.J. Steiner, S. Evans, I. Cerrillo, J. Mendez, G. Cabailh, S. O'Brien, J.W. Wells, I.T. McGovern and D.A. Evans, Growth and morphology of SnPc films on the S-GaAs(0 0 1) surface: a combined XPS, AFM and NEXAFS study 234 (2004) 131
Vearey-Roberts, A.R., see Cabailh, G. 234 (2004) 144
Vézian, S., F. Natali, F. Semond and J. Massies, Kinetic roughening during gas-source molecular-beam epitaxy of gallium nitride 234 (2004) 445
Vida, Gy., see Horváth, Z.J. 234 (2004) 67
Vobornik, D., see Cricenti, A. 234 (2004) 374

Wang, G., see Nešpůrek, S. 234 (2004) 395
Wang, S., see Fleischer, K. 234 (2004) 302
Watanabe, T., D. Yamasaki, K. Tatsumura and I. Ohdomari, Improved interatomic potential for stressed Si, O mixed systems 234 (2004) 207
Weijten, C, see van Elsbergen, V. 234 (2004) 120
Weiter, M., see Nešpůrek, S. 234 (2004) 395
Wells, J.W., see Cabailh, G. 234 (2004) 144
Wells, J.W., see Vearey-Roberts, A.R. 234 (2004) 131
Wilks, S.P., see Brown, M.R. 234 (2004) 434
Wilks, S.P., see Ferkel, H.S. 234 (2004) 2
Wilks, S.P., see Ferkel, H.S. 234 (2004) 82
Willander, M., see Semchuk, O.Yu. 234 (2004) 415

Wulfhekel, W., D. Sander, S. Nitsche, F. Dulot, A. Leycuras and M. Hanbücken, Structural reorganisation of vicinal surfaces on 6H-SiC(0001) induced by hot hydrogen etching 234 (2004) 251
Wulfhekel, W., see Kraus, A. 234 (2004) 307

Yamasaki, D., see Watanabe, T. 234 (2004) 207
Yamashita, Y., see Akagi, K. 234 (2004) 162
Yan, J., M.J. Kappers, Z.H. Barber and C.J. Humphreys, Effects of oxygen plasma treatments on the formation of ohmic contacts to GaN 234 (2004) 328
Yoshida, S., see Sato, T. 234 (2004) 11
Yoshida, T., see Hattori, T. 234 (2004) 197
Yoshida, Y., K. Akimoto, T. Emoto, S. Kikuchi, K. Itagaki and H. Namita, Lattice distortion due to surface treatment of bias sputtering revealed by extremely asymmetric X-ray diffraction 234 (2004) 409
Yoshinobu, J., see Akagi, K. 234 (2004) 162

Zahn, D.R.T., see Bekkali, A.-E.-H. 234 (2004) 149
Zahn, D.R.T., see Gavrila, G. 234 (2004) 126
Zahn, D.R.T., see Gorgoi, M. 234 (2004) 138
Zahn, D.R.T., see Kampen, T. 234 (2004) 313
Zahn, D.R.T., see Kampen, T. 234 (2004) 341
Zahn, D.R.T., see Kampen, T.U. 234 (2004) 333
Zahn, D.R.T., see König, D. 234 (2004) 222
Zahn, D.R.T., see Milekhin, A.G. 234 (2004) 45
Zahn, D.R.T., see Paez, B.A. 234 (2004) 168
Zahn, D.R.T., see Salvan, G. 234 (2004) 178
Zahn, D.R.T., see Silaghi, S.D. 234 (2004) 113
Zako, T., see Tanii, T. 234 (2004) 102
Zamoryarskaya, M.V., V.I. Sokolov and V. Plotnikov, Cathodoluminescence study of $Si/SiO_2$ interface structure 234 (2004) 214
Zanelatto, G., see Milekhin, A.G. 234 (2004) 45
Zaumseil, J., see van Elsbergen, V. 234 (2004) 120
Zhang, G.-J., see Tanii, T. 234 (2004) 102
Zhong, G., see Ferrer, D. 234 (2004) 72
Ziller, T., see Kampen, T. 234 (2004) 313

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Applied Surface Science 234 (2004) VIII–XVII

applied surface science

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# Subject Index


## *Aluminium*

Optical phonons in InAs and AlAs quantum dot structures, A.G. Milekhin, A.I. Toropov, A.K. Bakarov, M.Yu. Ladanov, G. Zanelatto, J.C. Galzerani, S. Schulze and D.R.T. Zahn 234 (2004) 45

Field effect of fixed negative charges on oxidized silicon induced by $AlF_3$ layers with fluorine deficiency, D. König, D.R.T. Zahn and G. Ebest 234 (2004) 222

Effects of oxygen plasma treatments on the formation of ohmic contacts to GaN, J. Yan, M.J. Kappers, Z.H. Barber and C.J. Humphreys 234 (2004) 328

## *Aluminium oxide*

Photoluminescence characteristics of rare earth-doped nanoporous aluminum oxide, W.M. de Azevedo, D.D. de Carvalho, E.A. de Vasconcelos and E.F. da Silva Jr. 234 (2004) 457

## *Antimony*

Influence of the substrate surface termination on the properties of bcc-cobalt films: GaAs(1 1 0) versus Sb/GaAs(1 1 0), M. Izquierdo, M.E. Dávila, C.M. Teodorescu, J. Chrost, H. Ascolani, J. Avila and M.C. Asensio 234 (2004) 468

## *Arsenic*

Optical phonons in InAs and AlAs quantum dot structures, A.G. Milekhin, A.I. Toropov, A.K. Bakarov, M.Yu. Ladanov, G. Zanelatto, J.C. Galzerani, S. Schulze and D.R.T. Zahn 234 (2004) 45

## *Atomic force microscopy*

Growth and morphology of SnPc films on the S-GaAs(0 0 1) surface: a combined XPS, AFM and NEXAFS study, A.R. Vearey-Roberts, H.J. Steiner, S. Evans, I. Cerrillo, J. Mendez, G. Cabailh, S. O'Brien, J.W. Wells, I.T. McGovern and D.A. Evans 234 (2004) 131

Mechanism of hydrogen, oxygen and humidity sensing by Cu/Pd-porous silicon–silicon structures, V.G. Litovchenko, T.I. Gorbanyuk, V.S. Solntsev and A.A. Evtukh 234 (2004) 262

Growth and modification of thin SiGeC films at low substrate temperatures through UV laser assisted processing, E. López, S. Chiussi, J. Serra, P. González, C. Serra, U. Kosch, B. León, F. Fabbri, L. Fornarini and S. Martelli 234 (2004) 422

Kinetic roughening during gas-source molecular-beam epitaxy of gallium nitride, S. Vézian, F. Natali, F. Semond and J. Massies 234 (2004) 445

## *Auger electron spectroscopy*

Reductions in interface defects, $D_{it}$, by post-oxidation plasma-assisted nitridation of GaN–$SiO_2$ interfaces in MOS devices, C. Bae and G. Lucovsky 234 (2004) 475

## *Boron*

Shallow boron dopant on silicon. An MD study, A. Mari Carmen Pérez-Martín, J.J. Jiménez-Rodríguez and J.C. Jiménez-Sáez 234 (2004) 228

Optical nanospectroscopy applications in material science, A. Cricenti, G. Longo, A. Ustione, V. Mussi, R. Generosi, M. Luce, M. Rinaldi, P. Perfetti, D. Vobornik, G. Margaritondo, J.S. Sanghera, P. Thielen, I.D. Aggarwal, B. Ivanov, J.K. Miller, R. Haglund, N.H. Tolk, A. Congiu-Castellano, M.A. Rizzo, D.W. Piston, F. Somma, G. Baldacchini, F. Bonfigli, T. Marolo, F. Flora, R.M. Montereali, A. Faenov and T. Pikuz 234 (2004) 374

## *Biological materials*

Metal deposition onto biomolecular layers on silicon surfaces: a study of interface forma-


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tion using Raman spectroscopy, S.D. Silaghi, R. Scholz, G. Salvan, Yu.J. Suzuki, M. Friedrich, T.U. Kampen and D.R.T. Zahn 234 (2004) 113

*Carbon*

Growth and modification of thin SiGeC films at low substrate temperatures through UV laser assisted processing, E. López, S. Chiussi, J. Serra, P. González, C. Serra, U. Kosch, B. León, F. Fabbri, L. Fornarini and S. Martelli 234 (2004) 422

*Chemical vapour deposition*

Nanostructural features of nc-Si:H thin films prepared by PECVD, J.-H. Shim, S. Im and N.-H. Cho 234 (2004) 268

Growth and modification of thin SiGeC films at low substrate temperatures through UV laser assisted processing, E. López, S. Chiussi, J. Serra, P. González, C. Serra, U. Kosch, B. León, F. Fabbri, L. Fornarini and S. Martelli 234 (2004) 422

Reductions in interface defects, $D_{it}$, by post-oxidation plasma-assisted nitridation of GaN–$SiO_2$ interfaces in MOS devices, C. Bae and G. Lucovsky 234 (2004) 475

*Cobalt*

Influence of the substrate surface termination on the properties of bcc-cobalt films: GaAs(1 1 0) versus Sb/GaAs(1 1 0), M. Izquierdo, M.E. Dávila, C.M. Teodorescu, J. Chrost, H. Ascolani, J. Avila and M.C. Asensio 234 (2004) 468

*Copper*

Thickness dependence of the LUMO position for phthalocyanines on hydrogen passivated silicon (1 1 1), M. Gorgoi, W. Michaelis, T.U. Kampen, D. Schlettwein and D.R.T. Zahn 234 (2004) 138

Mechanism of hydrogen, oxygen and humidity sensing by Cu/Pd-porous silicon–silicon structures, V.G. Litovchenko, T.I. Gorbanyuk, V.S. Solntsev and A.A. Evtukh 234 (2004) 262

*Density of state*

Barrier formation at metal–organic interfaces: dipole formation and the charge neutrality level, H. Vázquez, F. Flores, R. Oszwaldowski, J. Ortega, R. Pérez and A. Kahn 234 (2004) 107

*Depth profiling*

Growth and modification of thin SiGeC films at low substrate temperatures through UV laser assisted processing, E. López, S. Chiussi, J. Serra, P. González, C. Serra, U. Kosch, B. León, F. Fabbri, L. Fornarini and S. Martelli 234 (2004) 422

Atomic-scale depth profiling of composition, chemical structure and electronic band structure of $La_2O_3$/Si(1 0 0) interfacial transition layer, H. Nohira, T. Shiraishi, K. Takahashi, T. Hattori, I. Kashiwagi, C. Ohshima, S. Ohmi, H. Iwai, S. Joumori, K. Nakajima, M. Suzuki and K. Kimura 234 (2004) 493

*Doping effects*

Shallow boron dopant on silicon. An MD study, A. Mari Carmen Pérez-Martín, J.J. Jiménez-Rodríguez and J.C. Jiménez-Sáez 234 (2004) 228

Photoluminescence characteristics of rare earth-doped nanoporous aluminum oxide, W.M. de Azevedo, D.D. de Carvalho, E.A. de Vasconcelos and E.F. da Silva Jr. 234 (2004) 457

*Electrical properties*

Theoretical study of the adsorption of a PTCDA monolayer on S-passivated GaAs(1 0 0), B. Szűcs, Z. Hajnal, R. Scholz, S. Sanna and Th. Frauenheim 234 (2004) 173

Enhanced tunneling in stacked gate dielectrics with ultra-thin $HfO_2$ layers sandwiched between thicker $SiO_2$ layers, C.L. Hinkle, C. Fulton, R.J. Nemanich and G. Lucovsky 234 (2004) 240

Effects of oxygen plasma treatments on the formation of ohmic contacts to GaN, J. Yan, M.J. Kappers, Z.H. Barber and C.J. Humphreys 234 (2004) 328

*Electron diffraction*

Surface phase transitions at metal–semiconductor interfaces: a revisit is needed, M.E. Dávila, J. Avila, H. Ascolani, G. Le Lay, M. Göthelid, U.O. Karlsson and M.C. Asensio 234 (2004) 274

Influence of the substrate surface termination on the properties of bcc-cobalt films: GaAs(1 1 0) versus Sb/GaAs(1 1 0), M. Izquierdo, M.E. Dávila, C.M. Teodorescu, J. Chrost, H. Ascolani, J. Avila and M.C. Asensio 234 (2004) 468

*Electron microscopy*

Mechanism of hydrogen, oxygen and humidity sensing by Cu/Pd-porous silicon–silicon

structures, V.G. Litovchenko, T.I. Gorbanyuk, V.S. Solntsev and A.A. Evtukh 234 (2004) 262
Growth and modification of thin SiGeC films at low substrate temperatures through UV laser assisted processing, E. López, S. Chiussi, J. Serra, P. González, C. Serra, U. Kosch, B. León, F. Fabbri, L. Fornarini and S. Martelli 234 (2004) 422
Polarization anisotropy in the photoluminescence from InGaP layers grown by liquid phase epitaxy, T. Prutskij, P. Díaz-Arencibia, R.A. Brito-Orta, A. Mintairov, T. Kosel and J. Merz 234 (2004) 462

*Epitaxy*

Polarization anisotropy in the photoluminescence from InGaP layers grown by liquid phase epitaxy, T. Prutskij, P. Díaz-Arencibia, R.A. Brito-Orta, A. Mintairov, T. Kosel and J. Merz 234 (2004) 462

*Etching*

PL and EL features of p-type porous silicon prepared by electrochemical anodic etching, D.-A. Kim, J.-H. Shim and N.-H. Cho 234 (2004) 256

*Evaporation*

Growth and morphology of SnPc films on the S-GaAs(0 0 1) surface: a combined XPS, AFM and NEXAFS study, A.R. Vearey-Roberts, H.J. Steiner, S. Evans, I. Cerrillo, J. Mendez, G. Cabailh, S. O'Brien, J.W. Wells, I.T. McGovern and D.A. Evans 234 (2004) 131

*Gallium*

High-resolution photoemission study of the Si(111)/Au interface and its modification by a GaSe van der Waals termination layer, R. Fritsche, B. Jaeckel, A. Klein and W. Jaegermann 234 (2004) 321
Effects of oxygen plasma treatments on the formation of ohmic contacts to GaN, J. Yan, M.J. Kappers, Z.H. Barber and C.J. Humphreys 234 (2004) 328
Kinetic roughening during gas-source molecular-beam epitaxy of gallium nitride, S. Vézian, F. Natali, F. Semond and J. Massies 234 (2004) 445
Reductions in interface defects, $D_{it}$, by post-oxidation plasma-assisted nitridation of GaN–$SiO_2$ interfaces in MOS devices, C. Bae and G. Lucovsky 234 (2004) 475

*Gallium arsenide*

Inhomogeneous broadening arising from interface fluctuations in strained $In_xGa_{1-x}As$/GaAs and $(In_xGa_{1-x}As)_y(InP)_{1-y}$/InP quantum wells, C.L.N. Oliveira, J.A.K. Freire, V.N. Freire and G.A. Farias 234 (2004) 38
Growth and morphology of SnPc films on the S-GaAs(0 0 1) surface: a combined XPS, AFM and NEXAFS study, A.R. Vearey-Roberts, H.J. Steiner, S. Evans, I. Cerrillo, J. Mendez, G. Cabailh, S. O'Brien, J.W. Wells, I.T. McGovern and D.A. Evans 234 (2004) 131
Theoretical study of the adsorption of a PTCDA monolayer on S-passivated GaAs(1 0 0), B. Szűcs, Z. Hajnal, R. Scholz, S. Sanna and Th. Frauenheim 234 (2004) 173
Modification of GaAs(1 0 0) surfaces upon adsorption of perylene derivatives, G. Salvan, S. Silaghi, B. Paez, T.U. Kampen and D.R.T. Zahn 234 (2004) 178
Influence of the substrate surface termination on the properties of bcc-cobalt films: GaAs(1 1 0) versus Sb/GaAs(1 1 0), M. Izquierdo, M.E. Dávila, C.M. Teodorescu, J. Chrost, H. Ascolani, J. Avila and M.C. Asensio 234 (2004) 468

*Gallium phosphide*

Polarization anisotropy in the photoluminescence from InGaP layers grown by liquid phase epitaxy, T. Prutskij, P. Díaz-Arencibia, R.A. Brito-Orta, A. Mintairov, T. Kosel and J. Merz 234 (2004) 462

*Germanium*

Growth and modification of thin SiGeC films at low substrate temperatures through UV laser assisted processing, E. López, S. Chiussi, J. Serra, P. González, C. Serra, U. Kosch, B. León, F. Fabbri, L. Fornarini and S. Martelli 234 (2004) 422

*Gold*

Barrier formation at metal–organic interfaces: dipole formation and the charge neutrality level, H. Vázquez, F. Flores, R. Oszwaldowski, J. Ortega, R. Pérez and A. Kahn 234 (2004) 107
High-resolution photoemission study of the Si(111)/Au interface and its modification by a GaSe van der Waals termination layer, R. Fritsche, B. Jaeckel, A. Klein and W. Jaegermann 234 (2004) 321

*Hafnium*

Enhanced tunneling in stacked gate dielectrics with ultra-thin $HfO_2$ layers sandwiched

between thicker $SiO_2$ layers, C.L. Hinkle, C. Fulton, R.J. Nemanich and G. Lucovsky 234 (2004) 240
A spectroscopic study distinguishing between chemical phase separation with different degrees of crystallinity in Hf(Zr) silicate alloys, G. Lucovsky, G.B. Rayner, D. Kang, C.L. Hinkle and J.G. Hong 234 (2004) 429

## *Halogenides*

Methylchloride adsorbed on Si(0 0 1): an ab initio study, M. Preuss, W.G. Schmidt, K. Seino and F. Bechstedt 234 (2004) 155
Field effect of fixed negative charges on oxidized silicon induced by $AlF_3$ layers with fluorine deficiency, D. König, D.R.T. Zahn and G. Ebest 234 (2004) 222

## *Hydrocarbons*

Growth and morphology of SnPc films on the S-GaAs(0 0 1) surface: a combined XPS, AFM and NEXAFS study, A.R. Vearey-Roberts, H.J. Steiner, S. Evans, I. Cerrillo, J. Mendez, G. Cabailh, S. O'Brien, J.W. Wells, I.T. McGovern and D.A. Evans 234 (2004) 131
Thickness dependence of the LUMO position for phthalocyanines on hydrogen passivated silicon (1 1 1), M. Gorgoi, W. Michaelis, T.U. Kampen, D. Schlettwein and D.R.T. Zahn 234 (2004) 138
Methylchloride adsorbed on Si(0 0 1): an ab initio study, M. Preuss, W.G. Schmidt, K. Seino and F. Bechstedt 234 (2004) 155
Structural and chemical property of unsaturated cyclic-hydrocarbon molecules regularly chemisorbed on Si(0 0 1) surface, K. Akagi, S. Tsuneyuki, Y. Yamashita, K. Hamaguchi and J. Yoshinobu 234 (2004) 162

## *Hydrogen*

Thickness dependence of the LUMO position for phthalocyanines on hydrogen passivated silicon (1 1 1), M. Gorgoi, W. Michaelis, T.U. Kampen, D. Schlettwein and D.R.T. Zahn 234 (2004) 138
Mechanism of hydrogen, oxygen and humidity sensing by Cu/Pd-porous silicon–silicon structures, V.G. Litovchenko, T.I. Gorbanyuk, V.S. Solntsev and A.A. Evtukh 234 (2004) 262
Nanostructural features of nc-Si:H thin films prepared by PECVD, J.-H. Shim, S. Im and N.-H. Cho 234 (2004) 268

## *Indium*

Inhomogeneous broadening arising from interface fluctuations in strained $In_xGa_{1-x}As$/GaAs and $(In_xGa_{1-x}As)_y(InP)_{1-y}$/InP quantum wells, C.L.N. Oliveira, J.A.K. Freire, V.N. Freire and G.A. Farias 234 (2004) 38
Raman monitoring of In and Ag growth on PTCDA and DiMe-PTCDI thin films, B.A. Paez, G. Salvan, S. Silaghi, R. Scholz, T.U. Kampen and D.R.T. Zahn 234 (2004) 168
Atomic indium nanowires on Si(1 1 1): the (4 × 1)–(8 × 2) phase transition studied with reflectance anisotropy spectroscopy, K. Fleischer, S. Chandola, N. Esser, W. Richter, J.F. McGilp, W.G. Schmidt, S. Wang, W. Lu and J. Bernholc 234 (2004) 302
Polarization anisotropy in the photoluminescence from InGaP layers grown by liquid phase epitaxy, T. Prutskij, P. Díaz-Arencibia, R.A. Brito-Orta, A. Mintairov, T. Kosel and J. Merz 234 (2004) 462

## *Indium arsenide*

Optical phonons in InAs and AlAs quantum dot structures, A.G. Milekhin, A.I. Toropov, A.K. Bakarov, M.Yu. Ladanov, G. Zanelatto, J.C. Galzerani, S. Schulze and D.R.T. Zahn 234 (2004) 45

## *Indium phosphide*

Inhomogeneous broadening arising from interface fluctuations in strained $In_xGa_{1-x}As$/GaAs and $(In_xGa_{1-x}As)_y(InP)_{1-y}$/InP quantum wells, C.L.N. Oliveira, J.A.K. Freire, V.N. Freire and G.A. Farias 234 (2004) 38

## *Infrared spectroscopy*

Optical phonons in InAs and AlAs quantum dot structures, A.G. Milekhin, A.I. Toropov, A.K. Bakarov, M.Yu. Ladanov, G. Zanelatto, J.C. Galzerani, S. Schulze and D.R.T. Zahn 234 (2004) 45
Optical nanospectroscopy applications in material science, A. Cricenti, G. Longo, A. Ustione, V. Mussi, R. Generosi, M. Luce, M. Rinaldi, P. Perfetti, D. Vobornik, G. Margaritondo, J.S. Sanghera, P. Thielen, I.D. Aggarwal, B. Ivanov, J.K. Miller, R. Haglund, N.H. Tolk, A. Congiu-Castellano, M.A. Rizzo, D.W. Piston, F. Somma, G. Baldacchini, F. Bonfigli, T. Marolo, F. Flora, R.M. Montereali, A. Faenov and T. Pikuz 234 (2004) 374
A spectroscopic study distinguishing between chemical phase separation with different degrees of crystallinity in Hf(Zr) silicate alloys, G. Lucovsky, G.B. Rayner, D. Kang, C.L. Hinkle and J.G. Hong 234 (2004) 429

### *Interface*

Barrier formation at metal–organic interfaces: dipole formation and the charge neutrality level, H. Vázquez, F. Flores, R. Oszwaldowski, J. Ortega, R. Pérez and A. Kahn 234 (2004) 107

Metal deposition onto biomolecular layers on silicon surfaces: a study of interface formation using Raman spectroscopy, S.D. Silaghi, R. Scholz, G. Salvan, Yu.J. Suzuki, M. Friedrich, T.U. Kampen and D.R.T. Zahn 234 (2004) 113

Atomistic model structure of the Si(1 0 0)–$SiO_2$ interface from a synthesis of experimental data, A. Bongiorno and A. Pasquarello 234 (2004) 190

Dependence of $SiO_2$/Si interface structure on low-temperature oxidation process, T. Hattori, K. Azuma, Y. Nakata, M. Shioji, T. Shiraishi, T. Yoshida, K. Takahashi, H. Nohira, Y. Takata, S. Shin and K. Kobayashi 234 (2004) 197

$\delta(r)$ type model for interface defects in Si/$SiO_2$ nanocrystals, J.S. de Sousa, V.N. Freire and E.F. da Silva Jr. 234 (2004) 218

Surface phase transitions at metal–semiconductor interfaces: a revisit is needed, M.E. Dávila, J. Avila, H. Ascolani, G. Le Lay, M. Göthelid, U.O. Karlsson and M.C. Asensio 234 (2004) 274

High-resolution photoemission study of the Si(111)/Au interface and its modification by a GaSe van der Waals termination layer, R. Fritsche, B. Jaeckel, A. Klein and W. Jaegermann 234 (2004) 321

Reductions in interface defects, $D_{it}$, by post-oxidation plasma-assisted nitridation of GaN–$SiO_2$ interfaces in MOS devices, C. Bae and G. Lucovsky 234 (2004) 475

### *Ion scattering*

Atomistic model structure of the Si(1 0 0)–$SiO_2$ interface from a synthesis of experimental data, A. Bongiorno and A. Pasquarello 234 (2004) 190

Atomic-scale depth profiling of composition, chemical structure and electronic band structure of $La_2O_3$/Si(1 0 0) interfacial transition layer, H. Nohira, T. Shiraishi, K. Takahashi, T. Hattori, I. Kashiwagi, C. Ohshima, S. Ohmi, H. Iwai, S. Joumori, K. Nakajima, M. Suzuki and K. Kimura 234 (2004) 493

### *Lantanum*

Atomic-scale depth profiling of composition, chemical structure and electronic band structure of $La_2O_3$/Si(1 0 0) interfacial transition layer, H. Nohira, T. Shiraishi, K. Takahashi, T. Hattori, I. Kashiwagi, C. Ohshima, S. Ohmi, H. Iwai, S. Joumori, K. Nakajima, M. Suzuki and K. Kimura 234 (2004) 493

### *Laser processing*

Features of coherent laser beams interaction with condensed matter, O.Yu. Semchuk, R.V. Bila, M. Willander and M. Karlsteen 234 (2004) 415

Growth and modification of thin SiGeC films at low substrate temperatures through UV laser assisted processing, E. López, S. Chiussi, J. Serra, P. González, C. Serra, U. Kosch, B. León, F. Fabbri, L. Fornarini and S. Martelli 234 (2004) 422

### *Lithium*

Optical nanospectroscopy applications in material science, A. Cricenti, G. Longo, A. Ustione, V. Mussi, R. Generosi, M. Luce, M. Rinaldi, P. Perfetti, D. Vobornik, G. Margaritondo, J.S. Sanghera, P. Thielen, I.D. Aggarwal, B. Ivanov, J.K. Miller, R. Haglund, N.H. Tolk, A. Congiu-Castellano, M.A. Rizzo, D.W. Piston, F. Somma, G. Baldacchini, F. Bonfigli, T. Marolo, F. Flora, R.M. Montereali, A. Faenov and T. Pikuz 234 (2004) 374

### *Luminescence*

PL and EL features of p-type porous silicon prepared by electrochemical anodic etching, D.-A. Kim, J.-H. Shim and N.-H. Cho 234 (2004) 256

Nanostructural features of nc-Si:H thin films prepared by PECVD, J.-H. Shim, S. Im and N.-H. Cho 234 (2004) 268

Photoluminescence characteristics of rare earth-doped nanoporous aluminum oxide, W.M. de Azevedo, D.D. de Carvalho, E.A. de Vasconcelos and E.F. da Silva Jr. 234 (2004) 457

Polarization anisotropy in the photoluminescence from InGaP layers grown by liquid phase epitaxy, T. Prutskij, P. Díaz-Arencibia, R.A. Brito-Orta, A. Mintairov, T. Kosel and J. Merz 234 (2004) 462

### *Metals*

Barrier formation at metal–organic interfaces: dipole formation and the charge neutrality level, H. Vázquez, F. Flores, R. Oszwaldowski, J. Ortega, R. Pérez and A. Kahn 234 (2004) 107

Metal deposition onto biomolecular layers on silicon surfaces: a study of interface forma-

tion using Raman spectroscopy, S.D. Silaghi, R. Scholz, G. Salvan, Yu.J. Suzuki, M. Friedrich, T.U. Kampen and D.R.T. Zahn 234 (2004) 113
Surface phase transitions at metal–semiconductor interfaces: a revisit is needed, M.E. Dávila, J. Avila, H. Ascolani, G. Le Lay, M. Göthelid, U.O. Karlsson and M.C. Asensio 234 (2004) 274

## *Molecular beam epitaxy*

Kinetic roughening during gas-source molecular-beam epitaxy of gallium nitride, S. Vézian, F. Natali, F. Semond and J. Massies 234 (2004) 445

## *Molecular dynamics*

Structural and chemical property of unsaturated cyclic-hydrocarbon molecules regularly chemisorbed on Si(0 0 1) surface, K. Akagi, S. Tsuneyuki, Y. Yamashita, K. Hamaguchi and J. Yoshinobu 234 (2004) 162
Shallow boron dopant on silicon. An MD study, A. Mari Carmen Pérez-Martín, J.J. Jiménez-Rodríguez and J.C. Jiménez-Sáez 234 (2004) 228

## *Nanostructures*

$\delta(r)$ type model for interface defects in $Si/SiO_2$ nanocrystals, J.S. de Sousa, V.N. Freire and E.F. da Silva Jr. 234 (2004) 218
Nanostructural features of nc-Si:H thin films prepared by PECVD, J.-H. Shim, S. Im and N.-H. Cho 234 (2004) 268
Atomic indium nanowires on Si(1 1 1): the (4 × 1)–(8 × 2) phase transition studied with reflectance anisotropy spectroscopy, K. Fleischer, S. Chandola, N. Esser, W. Richter, J.F. McGilp, W.G. Schmidt, S. Wang, W. Lu and J. Bernholc 234 (2004) 302

## *Nitrides*

Effects of oxygen plasma treatments on the formation of ohmic contacts to GaN, J. Yan, M.J. Kappers, Z.H. Barber and C.J. Humphreys 234 (2004) 328
Kinetic roughening during gas-source molecular-beam epitaxy of gallium nitride, S. Vézian, F. Natali, F. Semond and J. Massies 234 (2004) 445
Reductions in interface defects, $D_{it}$, by post-oxidation plasma-assisted nitridation of GaN–$SiO_2$ interfaces in MOS devices, C. Bae and G. Lucovsky 234 (2004) 475

## *Optical properties*

Atomic indium nanowires on Si(1 1 1): the (4 × 1)–(8 × 2) phase transition studied with reflectance anisotropy spectroscopy, K. Fleischer, S. Chandola, N. Esser, W. Richter, J.F. McGilp, W.G. Schmidt, S. Wang, W. Lu and J. Bernholc 234 (2004) 302
Features of coherent laser beams interaction with condensed matter, O.Yu. Semchuk, R.V. Bila, M. Willander and M. Karlsteen 234 (2004) 415

## *Organic substances*

Barrier formation at metal–organic interfaces: dipole formation and the charge neutrality level, H. Vázquez, F. Flores, R. Oszwaldowski, J. Ortega, R. Pérez and A. Kahn 234 (2004) 107
Raman monitoring of In and Ag growth on PTCDA and DiMe-PTCDI thin films, B.A. Paez, G. Salvan, S. Silaghi, R. Scholz, T.U. Kampen and D.R.T. Zahn 234 (2004) 168
Theoretical study of the adsorption of a PTCDA monolayer on S-passivated GaAs(1 0 0), B. Szűcs, Z. Hajnal, R. Scholz, S. Sanna and Th. Frauenheim 234 (2004) 173
Modification of GaAs(1 0 0) surfaces upon adsorption of perylene derivatives, G. Salvan, S. Silaghi, B. Paez, T.U. Kampen and D.R.T. Zahn 234 (2004) 178

## *Oxidation*

Dependence of $SiO_2/Si$ interface structure on low-temperature oxidation process, T. Hattori, K. Azuma, Y. Nakata, M. Shioji, T. Shiraishi, T. Yoshida, K. Takahashi, H. Nohira, Y. Takata, S. Shin and K. Kobayashi 234 (2004) 197

## *Oxides*

Enhanced tunneling in stacked gate dielectrics with ultra-thin $HfO_2$ layers sandwiched between thicker $SiO_2$ layers, C.L. Hinkle, C. Fulton, R.J. Nemanich and G. Lucovsky 234 (2004) 240
A spectroscopic study distinguishing between chemical phase separation with different degrees of crystallinity in Hf(Zr) silicate alloys, G. Lucovsky, G.B. Rayner, D. Kang, C.L. Hinkle and J.G. Hong 234 (2004) 429
Atomic-scale depth profiling of composition, chemical structure and electronic band structure of $La_2O_3/Si(1\,0\,0)$ interfacial transition layer, H. Nohira, T. Shiraishi, K. Takahashi, T. Hattori, I. Kashiwagi, C. Ohshima, S. Ohmi, H. Iwai, S. Joumori, K. Nakajima, M. Suzuki and K. Kimura 234 (2004) 493

## *Oxygen*

Mechanism of hydrogen, oxygen and humidity sensing by Cu/Pd-porous silicon–silicon

structures, V.G. Litovchenko, T.I. Gorbanyuk, V.S. Solntsev and A.A. Evtukh 234 (2004) 262
Effects of oxygen plasma treatments on the formation of ohmic contacts to GaN, J. Yan, M.J. Kappers, Z.H. Barber and C.J. Humphreys 234 (2004) 328

### *Palladium*

Mechanism of hydrogen, oxygen and humidity sensing by Cu/Pd-porous silicon–silicon structures, V.G. Litovchenko, T.I. Gorbanyuk, V.S. Solntsev and A.A. Evtukh 234 (2004) 262

### *Phorus*

Optical phonons in InAs and AlAs quantum dot structures, A.G. Milekhin, A.I. Toropov, A.K. Bakarov, M.Yu. Ladanov, G. Zanelatto, J.C. Galzerani, S. Schulze and D.R.T. Zahn 234 (2004) 45

### *Phase transitions*

Surface phase transitions at metal–semiconductor interfaces: a revisit is needed, M.E. Dávila, J. Avila, H. Ascolani, G. Le Lay, M. Göthelid, U.O. Karlsson and M.C. Asensio 234 (2004) 274
Atomic indium nanowires on Si(1 1 1): the (4 × 1)–(8 × 2) phase transition studied with reflectance anisotropy spectroscopy, K. Fleischer, S. Chandola, N. Esser, W. Richter, J.F. McGilp, W.G. Schmidt, S. Wang, W. Lu and J. Bernholc 234 (2004) 302

### *Photoelectron spectroscopy*

Growth and morphology of SnPc films on the S-GaAs(0 0 1) surface: a combined XPS, AFM and NEXAFS study, A.R. Vearey-Roberts, H.J. Steiner, S. Evans, I. Cerrillo, J. Mendez, G. Cabailh, S. O'Brien, J.W. Wells, I.T. McGovern and D.A. Evans 234 (2004) 131
Thickness dependence of the LUMO position for phthalocyanines on hydrogen passivated silicon (1 1 1), M. Gorgoi, W. Michaelis, T.U. Kampen, D. Schlettwein and D.R.T. Zahn 234 (2004) 138
Dependence of $SiO_2$/Si interface structure on low-temperature oxidation process, T. Hattori, K. Azuma, Y. Nakata, M. Shioji, T. Shiraishi, T. Yoshida, K. Takahashi, H. Nohira, Y. Takata, S. Shin and K. Kobayashi 234 (2004) 197
High-resolution photoemission study of the Si(111)/Au interface and its modification by a GaSe van der Waals termination layer, R. Fritsche, B. Jaeckel, A. Klein and W. Jaegermann 234 (2004) 321
Effects of oxygen plasma treatments on the formation of ohmic contacts to GaN, J. Yan, M.J. Kappers, Z.H. Barber and C.J. Humphreys 234 (2004) 328
Growth and modification of thin SiGeC films at low substrate temperatures through UV laser assisted processing, E. López, S. Chiussi, J. Serra, P. González, C. Serra, U. Kosch, B. León, F. Fabbri, L. Fornarini and S. Martelli 234 (2004) 422
A spectroscopic study distinguishing between chemical phase separation with different degrees of crystallinity in Hf(Zr) silicate alloys, G. Lucovsky, G.B. Rayner, D. Kang, C.L. Hinkle and J.G. Hong 234 (2004) 429
Influence of the substrate surface termination on the properties of bcc-cobalt films: GaAs(1 1 0) versus Sb/GaAs(1 1 0), M. Izquierdo, M.E. Dávila, C.M. Teodorescu, J. Chrost, H. Ascolani, J. Avila and M.C. Asensio 234 (2004) 468
Atomic-scale depth profiling of composition, chemical structure and electronic band structure of $La_2O_3$/Si(1 0 0) interfacial transition layer, H. Nohira, T. Shiraishi, K. Takahashi, T. Hattori, I. Kashiwagi, C. Ohshima, S. Ohmi, H. Iwai, S. Joumori, K. Nakajima, M. Suzuki and K. Kimura 234 (2004) 493

### *Plasma processing*

Nanostructural features of nc-Si:H thin films prepared by PECVD, J.-H. Shim, S. Im and N.-H. Cho 234 (2004) 268
Effects of oxygen plasma treatments on the formation of ohmic contacts to GaN, J. Yan, M.J. Kappers, Z.H. Barber and C.J. Humphreys 234 (2004) 328
Reductions in interface defects, $D_{it}$, by post-oxidation plasma-assisted nitridation of GaN–$SiO_2$ interfaces in MOS devices, C. Bae and G. Lucovsky 234 (2004) 475

### *Polymer*

Mechanism of hydrogen, oxygen and humidity sensing by Cu/Pd-porous silicon–silicon structures, V.G. Litovchenko, T.I. Gorbanyuk, V.S. Solntsev and A.A. Evtukh 234 (2004) 262

### *Quantum effects*

Inhomogeneous broadening arising from interface fluctuations in strained $In_xGa_{1-x}As$/GaAs and $(In_nGa_{1-n}As)_x(InP)_{1-x}$/InP

quantum wells, C.L.N. Oliveira, J.A.K. Freire, V.N. Freire and G.A. Farias 234 (2004) 38
Optical phonons in InAs and AlAs quantum dot structures, A.G. Milekhin, A.I. Toropov, A.K. Bakarov, M.Yu. Ladanov, G. Zanelatto, J.C. Galzerani, S. Schulze and D.R.T. Zahn 234 (2004) 45
$\delta(r)$ type model for interface defects in $Si/SiO_2$ nanocrystals, J.S. de Sousa, V.N. Freire and E.F. da Silva Jr. 234 (2004) 218

### *Raman scattering*

Optical phonons in InAs and AlAs quantum dot structures, A.G. Milekhin, A.I. Toropov, A.K. Bakarov, M.Yu. Ladanov, G. Zanelatto, J.C. Galzerani, S. Schulze and D.R.T. Zahn 234 (2004) 45
Metal deposition onto biomolecular layers on silicon surfaces: a study of interface formation using Raman spectroscopy, S.D. Silaghi, R. Scholz, G. Salvan, Yu.J. Suzuki, M. Friedrich, T.U. Kampen and D.R.T. Zahn 234 (2004) 113
Raman monitoring of In and Ag growth on PTCDA and DiMe-PTCDI thin films, B.A. Paez, G. Salvan, S. Silaghi, R. Scholz, T.U. Kampen and D.R.T. Zahn 234 (2004) 168
Modification of GaAs(1 0 0) surfaces upon adsorption of perylene derivatives, G. Salvan, S. Silaghi, B. Paez, T.U. Kampen and D.R.T. Zahn 234 (2004) 178

### *Rare earth metals*

Photoluminescence characteristics of rare earth-doped nanoporous aluminum oxide, W.M. de Azevedo, D.D. de Carvalho, E.A. de Vasconcelos and E.F. da Silva Jr. 234 (2004) 457

### *Scanning near field optical microscopy*

Optical nanospectroscopy applications in material science, A. Cricenti, G. Longo, A. Ustione, V. Mussi, R. Generosi, M. Luce, M. Rinaldi, P. Perfetti, D. Vobornik, G. Margaritondo, J.S. Sanghera, P. Thielen, I.D. Aggarwal, B. Ivanov, J.K. Miller, R. Haglund, N.H. Tolk, A. Congiu-Castellano, M.A. Rizzo, D.W. Piston, F. Somma, G. Baldacchini, F. Bonfigli, T. Marolo, F. Flora, R.M. Montereali, A. Faenov and T. Pikuz 234 (2004) 374

### *Scanning tunneling microscopy*

Structural and chemical property of unsaturated cyclic-hydrocarbon molecules regularly chemisorbed on Si(0 0 1) surface, K. Akagi, S. Tsuneyuki, Y. Yamashita, K. Hamaguchi and J. Yoshinobu 234 (2004) 162
Si-substitutional defects on the $\alpha$-Sn/Si(1 1 1)-$(\sqrt{3} \times \sqrt{3})$ surface, W. Kaminski, P. Jelinek, R. Pérez, F. Flores and J. Ortega 234 (2004) 286
Comparison of structural re-organisations observed on pre-patterned vicinal Si(1 1 1) and Si(1 0 0) surfaces during heat treatment, A. Kraus, H. Neddermeyer, W. Wulfhekel, D. Sander, T. Maroutian, F. Dulot, A. Martinez-Gil and M. Hanbücken 234 (2004) 307

### *Schottky barrier*

Mechanism of hydrogen, oxygen and humidity sensing by Cu/Pd-porous silicon–silicon structures, V.G. Litovchenko, T.I. Gorbanyuk, V.S. Solntsev and A.A. Evtukh 234 (2004) 262
High-resolution photoemission study of the Si(111)/Au interface and its modification by a GaSe van der Waals termination layer, R. Fritsche, B. Jaeckel, A. Klein and W. Jaegermann 234 (2004) 321

### *Selenium*

High-resolution photoemission study of the Si(111)/Au interface and its modification by a GaSe van der Waals termination layer, R. Fritsche, B. Jaeckel, A. Klein and W. Jaegermann 234 (2004) 321

### *Semiconductors*

Surface phase transitions at metal–semiconductor interfaces: a revisit is needed, M.E. Dávila, J. Avila, H. Ascolani, G. Le Lay, M. Göthelid, U.O. Karlsson and M.C. Asensio 234 (2004) 274
Features of coherent laser beams interaction with condensed matter, O.Yu. Semchuk, R.V. Bila, M. Willander and M. Karlsteen 234 (2004) 415

### *Silane*

Nanostructural features of nc-Si:H thin films prepared by PECVD, J.-H. Shim, S. Im and N.-H. Cho 234 (2004) 268

### *Silicon*

Metal deposition onto biomolecular layers on silicon surfaces: a study of interface formation using Raman spectroscopy, S.D. Sila-

ghi, R. Scholz, G. Salvan, Yu.J. Suzuki, M. Friedrich, T.U. Kampen and D.R.T. Zahn 234 (2004) 113
Thickness dependence of the LUMO position for phthalocyanines on hydrogen passivated silicon (1 1 1), M. Gorgoi, W. Michaelis, T.U. Kampen, D. Schlettwein and D.R.T. Zahn 234 (2004) 138
Methylchloride adsorbed on Si(0 0 1): an ab initio study, M. Preuss, W.G. Schmidt, K. Seino and F. Bechstedt 234 (2004) 155
Structural and chemical property of unsaturated cyclic-hydrocarbon molecules regularly chemisorbed on Si(0 0 1) surface, K. Akagi, S. Tsuneyuki, Y. Yamashita, K. Hamaguchi and J. Yoshinobu 234 (2004) 162
Atomistic model structure of the Si(1 0 0)–$SiO_2$ interface from a synthesis of experimental data, A. Bongiorno and A. Pasquarello 234 (2004) 190
Dependence of $SiO_2$/Si interface structure on low-temperature oxidation process, T. Hattori, K. Azuma, Y. Nakata, M. Shioji, T. Shiraishi, T. Yoshida, K. Takahashi, H. Nohira, Y. Takata, S. Shin and K. Kobayashi 234 (2004) 197
$\delta(r)$ type model for interface defects in Si/$SiO_2$ nanocrystals, J.S. de Sousa, V.N. Freire and E.F. da Silva Jr. 234 (2004) 218
Field effect of fixed negative charges on oxidized silicon induced by $AlF_3$ layers with fluorine deficiency, D. König, D.R.T. Zahn and G. Ebest 234 (2004) 222
Shallow boron dopant on silicon. An MD study, A. Mari Carmen Pérez-Martín, J.J. Jiménez-Rodríguez and J.C. Jiménez-Sáez 234 (2004) 228
PL and EL features of p-type porous silicon prepared by electrochemical anodic etching, D.-A. Kim, J.-H. Shim and N.-H. Cho 234 (2004) 256
Mechanism of hydrogen, oxygen and humidity sensing by Cu/Pd-porous silicon–silicon structures, V.G. Litovchenko, T.I. Gorbanyuk, V.S. Solntsev and A.A. Evtukh 234 (2004) 262
Nanostructural features of nc-Si:H thin films prepared by PECVD, J.-H. Shim, S. Im and N.-H. Cho 234 (2004) 268
Si-substitutional defects on the α-Sn/Si(1 1 1)-($\sqrt{3} \times \sqrt{3}$) surface, W. Kaminski, P. Jelinek, R. Pérez, F. Flores and J. Ortega 234 (2004) 286
Atomic indium nanowires on Si(1 1 1): the (4 × 1)–(8 × 2) phase transition studied with reflectance anisotropy spectroscopy, K. Fleischer, S. Chandola, N. Esser, W. Richter, J.F. McGilp, W.G. Schmidt, S. Wang, W. Lu and J. Bernholc 234 (2004) 302
Comparison of structural re-organisations observed on pre-patterned vicinal Si(1 1 1) and Si(1 0 0) surfaces during heat treatment, A. Kraus, H. Neddermeyer, W. Wulfhekel, D. Sander, T. Maroutian, F. Dulot, A. Martínez-Gil and M. Hanbücken 234 (2004) 307
High-resolution photoemission study of the Si(111)/Au interface and its modification by a GaSe van der Waals termination layer, R. Fritsche, B. Jaeckel, A. Klein and W. Jaegermann 234 (2004) 321
Growth and modification of thin SiGeC films at low substrate temperatures through UV laser assisted processing, E. López, S. Chiussi, J. Serra, P. González, C. Serra, U. Kosch, B. León, F. Fabbri, L. Fornarini and S. Martelli 234 (2004) 422

## *Silicon oxide*

Atomistic model structure of the Si(1 0 0)–$SiO_2$ interface from a synthesis of experimental data, A. Bongiorno and A. Pasquarello 234 (2004) 190
Dependence of $SiO_2$/Si interface structure on low-temperature oxidation process, T. Hattori, K. Azuma, Y. Nakata, M. Shioji, T. Shiraishi, T. Yoshida, K. Takahashi, H. Nohira, Y. Takata, S. Shin and K. Kobayashi 234 (2004) 197
$\delta(r)$ type model for interface defects in Si/$SiO_2$ nanocrystals, J.S. de Sousa, V.N. Freire and E.F. da Silva Jr. 234 (2004) 218
Field effect of fixed negative charges on oxidized silicon induced by $AlF_3$ layers with fluorine deficiency, D. König, D.R.T. Zahn and G. Ebest 234 (2004) 222
Enhanced tunneling in stacked gate dielectrics with ultra-thin $HfO_2$ layers sandwiched between thicker $SiO_2$ layers, C.L. Hinkle, C. Fulton, R.J. Nemanich and G. Lucovsky 234 (2004) 240
A spectroscopic study distinguishing between chemical phase separation with different degrees of crystallinity in Hf(Zr) silicate alloys, G. Lucovsky, G.B. Rayner, D. Kang, C.L. Hinkle and J.G. Hong 234 (2004) 429
Reductions in interface defects, $D_{it}$, by post-oxidation plasma-assisted nitridation of GaN–$SiO_2$ interfaces in MOS devices, C. Bae and G. Lucovsky 234 (2004) 475

## *Silver*

Raman monitoring of In and Ag growth on PTCDA and DiMe-PTCDI thin films, B.A. Paez, G. Salvan, S. Silaghi, R. Scholz, T.U. Kampen and D.R.T. Zahn 234 (2004) 168

## *Sulphur*

Theoretical study of the adsorption of a PTCDA monolayer on S-passivated GaAs(1 0 0), B. Szűcs, Z. Hajnal, R. Scholz, S. Sanna and Th. Frauenheim 234 (2004) 173

### *Surface roughness*

Kinetic roughening during gas-source molecular-beam epitaxy of gallium nitride, S. Vézian, F. Natali, F. Semond and J. Massies 234 (2004) 445

### *Thin films*

Growth and morphology of SnPc films on the S-GaAs(0 0 1) surface: a combined XPS, AFM and NEXAFS study, A.R. Vearey-Roberts, H.J. Steiner, S. Evans, I. Cerrillo, J. Mendez, G. Cabailh, S. O'Brien, J.W. Wells, I.T. McGovern and D.A. Evans 234 (2004) 131

Nanostructural features of nc-Si:H thin films prepared by PECVD, J.-H. Shim, S. Im and N.-H. Cho 234 (2004) 268

Growth and modification of thin SiGeC films at low substrate temperatures through UV laser assisted processing, E. López, S. Chiussi, J. Serra, P. González, C. Serra, U. Kosch, B. León, F. Fabbri, L. Fornarini and S. Martelli 234 (2004) 422

### *Tin*

Growth and morphology of SnPc films on the S-GaAs(0 0 1) surface: a combined XPS, AFM and NEXAFS study, A.R. Vearey-Roberts, H.J. Steiner, S. Evans, I. Cerrillo, J. Mendez, G. Cabailh, S. O'Brien, J.W. Wells, I.T. McGovern and D.A. Evans 234 (2004) 131

Si-substitutional defects on the α-Sn/Si(1 1 1)-($\sqrt{3} \times \sqrt{3}$) surface, W. Kaminski, P. Jelinek, R. Pérez, F. Flores and J. Ortega 234 (2004) 286

### *Titanium*

Effects of oxygen plasma treatments on the formation of ohmic contacts to GaN, J. Yan, M.J. Kappers, Z.H. Barber and C.J. Humphreys 234 (2004) 328

### *Tunneling*

Enhanced tunneling in stacked gate dielectrics with ultra-thin $HfO_2$ layers sandwiched between thicker $SiO_2$ layers, C.L. Hinkle, C. Fulton, R.J. Nemanich and G. Lucovsky 234 (2004) 240

### *X-ray absorption*

Growth and morphology of SnPc films on the S-GaAs(0 0 1) surface: a combined XPS, AFM and NEXAFS study, A.R. Vearey-Roberts, H.J. Steiner, S. Evans, I. Cerrillo, J. Mendez, G. Cabailh, S. O'Brien, J.W. Wells, I.T. McGovern and D.A. Evans 234 (2004) 131

A spectroscopic study distinguishing between chemical phase separation with different degrees of crystallinity in Hf(Zr) silicate alloys, G. Lucovsky, G.B. Rayner, D. Kang, C.L. Hinkle and J.G. Hong 234 (2004) 429

### *X-ray diffraction*

Surface phase transitions at metal–semiconductor interfaces: a revisit is needed, M.E. Dávila, J. Avila, H. Ascolani, G. Le Lay, M. Göthelid, U.O. Karlsson and M.C. Asensio 234 (2004) 274

A spectroscopic study distinguishing between chemical phase separation with different degrees of crystallinity in Hf(Zr) silicate alloys, G. Lucovsky, G.B. Rayner, D. Kang, C.L. Hinkle and J.G. Hong 234 (2004) 429

Photoluminescence characteristics of rare earth-doped nanoporous aluminum oxide, W.M. de Azevedo, D.D. de Carvalho, E.A. de Vasconcelos and E.F. da Silva Jr. 234 (2004) 457

### *Zirconium*

A spectroscopic study distinguishing between chemical phase separation with different degrees of crystallinity in Hf(Zr) silicate alloys, G. Lucovsky, G.B. Rayner, D. Kang, C.L. Hinkle and J.G. Hong 234 (2004) 429